

1. A circuit arrangement
 - having a terminal (1) for a high-frequency signal,
 - having at least two additional signal leads (21a, 21b, 21c, 22a, 22b) which form
 - 5 transmission/reception paths,
 - having a switching unit (3) for connecting the terminal (1) to a signal lead (21a, 21b, 21c, 22a, 22b),
 - having a primary protection device (41) against electrostatic discharges which is connected between the terminal (1) and the switching unit (3),
 - 10 - wherein the primary protection device (41) contains a first protective element (51) which diverts all voltage pulses whose pulse height exceeds 200 V to reference potential (7),
 - wherein the first protective element (51) has a capacitance (8) which is less than 1 pF,
 - 15 - wherein the first protective element (51) has an insertion loss which is less than 0.3 dB,
 - wherein the switching unit (3) and the primary protection device (41) are integrated in or on a multilayer substrate.
- 20 2. The circuit arrangement as recited in claim 1,
wherein the first protective element (51) is a gallium arsenide double diode.

3. The circuit arrangement as recited in claim 1 or 2,
wherein the primary protection device (41) contains a lead (6), which connects the
terminal (1) to the switching unit (3) and wherein the first protective element (51)
connects the lead (6) to the reference potential (7).

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4. The circuit arrangement as recited in one of claims 1 through 3,
wherein a second protective element (52) is connected in parallel to the first
protective element (51).

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5. The circuit arrangement as recited in claim 4,
wherein a capacitor (8) is connected in series to the lead (6) between the first
protective element (51) and the second protective element (52).

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6. The circuit arrangement as recited in one of claims 4 or 5,
wherein the second protective element (52) is a spark gap.

7. The circuit arrangement as recited in one of claims 4 or 5,
wherein the second protective element (52) is a polymer suppressor.

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8. The circuit arrangement as recited in one of claims 4 or 5,
wherein the second protective element (52) is an overvoltage component whose
capacitance is smaller than 1 pF.

9. The circuit arrangement as recited in one of claims 4 or 5,
wherein the second protective element (52) is an inductance greater than 18 nH.

5 10. The circuit arrangement as recited in one of claims 1 through 9,
- wherein one or a plurality of control leads (91, 92, 93) are provided for the
control of the switching unit,
- wherein each control lead (91, 92, 93) is connected to a secondary protection
device (42) against electrostatic discharges.

10 11. The circuit arrangement as recited in one of claims 1 through 10,
wherein a supply lead (100) for an operating voltage (VCC) is provided, the
supply lead being connected to a secondary protection device (42) against electrostatic
discharges.

15 12. The circuit arrangement as recited in one of claims 1 through 11,
- wherein the switching unit (3) contains two field effect transistors (111, 112),
the break distance (121, 122) of each field effect transistor (111, 112) connecting the
terminal (1) to a signal lead (21a, 21b, 21c, 22a, 22b),
20 - wherein each gate (131, 132) of each field effect transistor (111, 112) is
connected to a control lead (91, 92),

- and wherein each gate (131, 132, 93) is connected to a secondary protection device (42) against electrostatic discharges.

13. The circuit arrangement as recited in one of claims 10 through 12,
5 wherein a secondary protection device (42) contains a protective element (53a, 53b, 53c, 54) having a switching voltage that is lower than 100 V.

14. The circuit arrangement as recited in one of claims 10 through 13,
wherein a secondary protection device (42) contains a protective element (53a,
10 53b, 53c, 54) which is a varistor.

15. The circuit arrangement as recited in one of claims 10 through 13,
wherein a secondary protection device (42) contains a protective element (53a,
53b, 53c, 54) which is a Zener diode.

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16. The circuit arrangement as recited in one of claims 10 through 15,
wherein the one or a plurality of secondary protection devices (42) is connected to
the reference potential (7).

20 17. The circuit arrangement as recited in one of claims 1 through 16,
wherein the switching unit (3) contains PIN diodes.

18. The circuit arrangement as recited in one of claims 1 through 16,
wherein the switching unit (3) contains a gallium arsenide switch.

19. The circuit arrangement as recited in one of claims 1 through 18,
5 wherein the terminal (1) is the antenna input of a mobile telephone.

20. The circuit arrangement as recited in one of claims 1 through 19,
wherein the signal leads (21a, 21b, 21c, 22a, 22b) form transmission/reception
paths of a mobile telephone.

10 21. The circuit arrangement as recited in one of claims 1 through 20,
wherein the switching unit (3) and the primary protection device (41) are
integrated in a multilayer ceramic substrate.